Hex Inverter

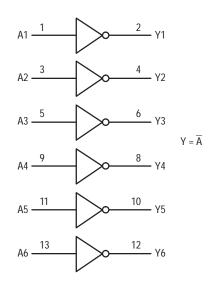
High-Performance Silicon-Gate CMOS

The MC74HC04A is identical in pinout to the LS04 and the MC14069. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

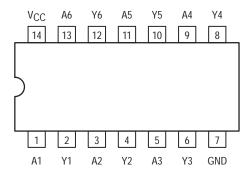
The device consists of six three-stage inverters.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 36 FETs or 9 Equivalent Gates

LOGIC DIAGRAM



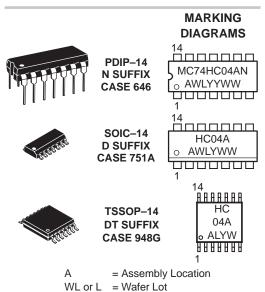
Pinout: 14-Lead Packages (Top View)





ON Semiconductor

http://onsemi.com



WW or W = Work Week

YY or Y = Year

FUNCTION TABLE

Inputs	Outputs
Α	Υ
L	Н
Н	L

ORDERING INFORMATION

Device	Package	Shipping
MC74HC04AN	PDIP-14	2000 / Box
MC74HC04AD	SOIC-14	55 / Rail
MC74HC04ADR2	SOIC-14	2500 / Reel
MC74HC04ADT	TSSOP-14	96 / Rail
MC74HC04ADTR2	TSSOP-14	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/ $^{\circ}$ C from 65 $^{\circ}$ to 125 $^{\circ}$ C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			VCC	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	(Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

DC CHARACTERISTICS (Voltages Referenced to GND)

			VCC	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{Out} = 0.1V \text{ or } V_{CC} -0.1V$ $ I_{Out} \le 20 \mu A$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
VIL	Maximum Low–Level Input Voltage	$V_{Out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{Out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
VOH	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20μΑ	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{array}{c cccc} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4\text{mA} \\ & I_{out} \leq 4.0\text{mA} \\ & I_{out} \leq 5.2\text{mA} \end{array} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{Out} ≤ 20μΑ	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{aligned} V_{\text{in}} &= V_{\text{IH}} \text{ or } V_{\text{IL}} & & I_{\text{out}} \leq 2.4 \text{mA} \\ & I_{\text{out}} \leq 4.0 \text{mA} \\ & I_{\text{out}} \leq 5.2 \text{mA} \end{aligned} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
lin	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μА
lcc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0μA	6.0	1.0	10	40	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50pF$, Input $t_f = t_f = 6ns$)

		v _{CC}	Gu	Guaranteed Limit		
Symbol	Parameter	V	–55 to 25°C	≤85°C	≤125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V		
C_{PD}	Power Dissipation Capacitance (Per Inverter)*	20	pF	ı

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

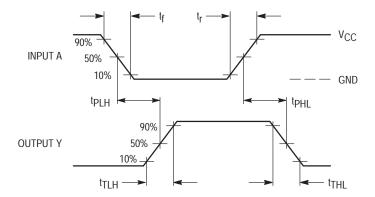
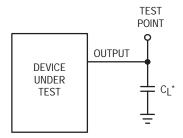


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

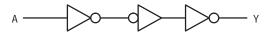
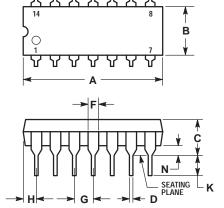


Figure 3. Expanded Logic Diagram (1/6 of the Device Shown)

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L



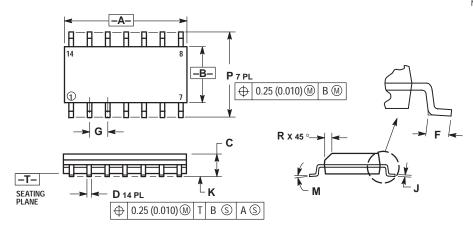


- NOTES:
 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
 2. DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 3. DIMENSION B DOES NOT INCLUDE MOLD

 - FLASH.
 4. ROUNDED CORNERS OPTIONAL

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300	BSC	7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



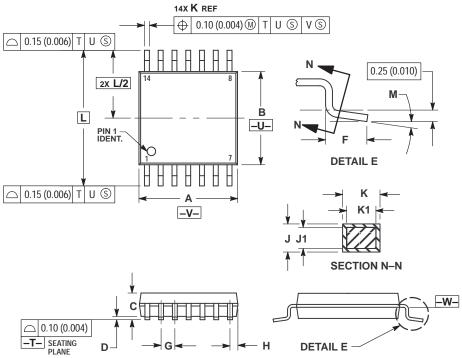
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI

- 1. DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWARD F. DAMBAR.
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
В	0.25	0.50	0.010	0.010

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS INCH		HES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007 0.010	
L	6.40		0.252 BSC	
M	0°	8°	0°	8 °

Notes

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303-308-7140 (M-F 1:00pm to 5:00pm Munich Time)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, England, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81–3–5740–2745 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.